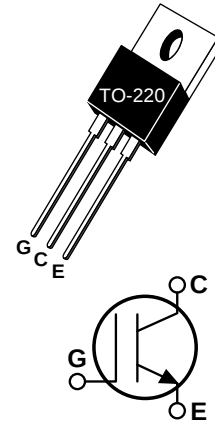


Fast IGBT

The Fast IGBT is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Fast IGBT offers superior ruggedness, fast switching speed and low Collector-Emitter On voltage.

- Low Forward Voltage Drop
- Low Tail Current
- Avalanche Rated
- High Freq. Switching to 20KHz
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT11GF120KR	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{CGR}	Collector-Gate Voltage ($R_{GE} = 20K\Omega$)	1200	
V_{EC}	Emitter-Collector Voltage	15	
V_{GE}	Gate-Emitter Voltage	± 20	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	22	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	11	
I_{CM1}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	44	
I_{CM2}	Pulsed Collector Current ^① @ $T_C = 110^\circ\text{C}$	22	
E_{AS}	Single Pulse Avalanche Energy ^②	10	mJ
P_D	Total Power Dissipation	125	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 0.4mA$)	1200			Volts
RBV_{CES}	Collector-Emitter Reverse Breakdown Voltage ($V_{GE} = 0V, I_C = 50mA$)	-15			
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 350\mu A, T_J = 25^\circ\text{C}$)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_J = 25^\circ\text{C}$)		2.5	3.0	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_J = 125^\circ\text{C}$)		3.1	3.7	
I_{CES}	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 25^\circ\text{C}$)			0.4	mA
	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 125^\circ\text{C}$)			2.0	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V, V_{CE} = 0V$)			± 100	nA



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT11GF120KR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{ies}	Input Capacitance	Capacitance V _{GE} = 0V V _{CE} = 25V f = 1 MHz		600	800	pF
C _{oes}	Output Capacitance			70	105	
C _{res}	Reverse Transfer Capacitance			38	55	
Q _g	Total Gate Charge ③	Gate Charge V _{GE} = 15V V _{CC} = 0.5V _{CES} I _C = I _{C2}		55		nC
Q _{ge}	Gate-Emitter Charge			35		
Q _{gc}	Gate-Collector ("Miller") Charge			6		
t _{d(on)}	Turn-on Delay Time	Resistive Switching (25°C) V _{GE} = 15V V _{CC} = 0.8V _{CES} I _C = I _{C2} R _G = 10Ω		10		ns
t _r	Rise Time			45		
t _{d(off)}	Turn-off Delay Time			55		
t _f	Fall Time			110		
t _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +150°C		13		ns
t _r	Rise Time			12		
t _{d(off)}	Turn-off Delay Time			125		
t _f	Fall Time			90		
E _{on}	Turn-on Switching Energy			.45		mJ
E _{off}	Turn-off Switching Energy			1.00		
E _{ts}	Total Switching Losses			1.45		
t _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +25°C		13		ns
t _r	Rise Time			12		
t _{d(off)}	Turn-off Delay Time			110		
t _f	Fall Time			90		
E _{ts}	Total Switching Losses			1.0		mJ
g _{fe}	Forward Transconductance	V _{CE} = 20V, I _C = I _{C2}	4.7			S

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{ΘJC}	Junction to Case			1.00	°C/W
R _{ΘJA}	Junction to Ambient			80	
Torque	Mounting Torque using a 6-32 or 3mm Binding Head Machine Screw		10		lb•in

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② I_C = 15A, R_{GE} = 25Ω, L = 300μH, T_J = 25°C

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.